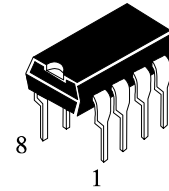


# IL358N

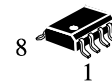
## Low Power Dual Operational Amplifier

The IL358 contains two independent high gain operational amplifiers with internal frequency compensation. The op-amps operate over a wide voltage range. The low power drain makes the IL358 a good choice for battery operation.

- Internally frequency compensated for unity gain
- Large DC voltage gain
- Single or Split Supply Operation
- Input common-mode voltage range to ground
- Large output voltage swing: 0V DC to  $V_{CC}-1.5V$  DC
- Power drain suitable for battery operation
- Low input offset voltage and offset current
- Differential input voltage range equal to the power supply voltage



N SUFFIX  
PLASTIC



D SUFFIX  
SOIC

### ORDERING INFORMATION

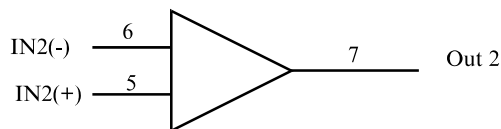
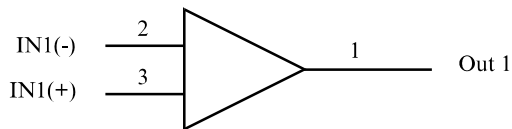
IL358N Plastic

IL358D SOIC

IZ358 Chip

$T_A = 0^\circ$  to  $70^\circ$  C for all packages

### BLOCK DIAGRAM



PIN 4 = GND  
PIN 8 =  $V_{CC}$

## IL358N

### MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
$V_{CC}$	Power Supply Voltages Single Supply Split Supplies	32 $\pm 16$	V
$V_{IDR}$	Input Differential Voltage Range (1)	$\pm 32$	V
$V_{ICR}$	Input Common Mode Voltage Range	-0.3 to 32	V
$t_S$	Short-Circuit duration of Output	100	ms
$I_{IN}$	Input Current, per pin (2)	50	mA
$T_J$	Junction Temperature Plastic Packages	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature Plastic Packages	-55 to +125	$^{\circ}\text{C}$
$T_L$	Lead Temperature, 1mm from Case for 10 Seconds	260	$^{\circ}\text{C}$

\*Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

Notes:

1. Split Power Supplies.
2.  $V_{IN} < -0.3\text{V}$

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
$V_{CC}$	DC Supply Voltage	$\pm 2.5$ or 5.0	$\pm 15$ or 30	V
$T_A$	Operating Temperature, All Package Types	0	+70	$^{\circ}\text{C}$

## IL358N

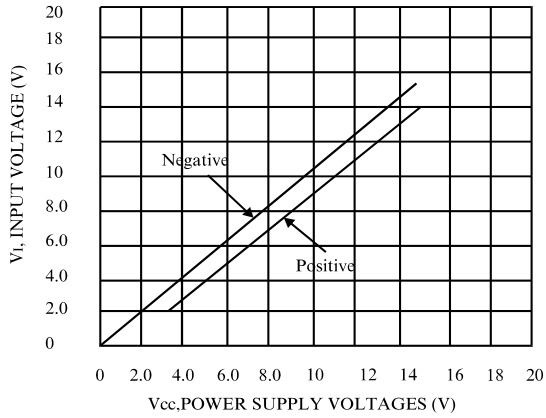
### DC ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=0 ÷ +70°C)

Symbol	Parameter	Test Conditions	Guaranteed Limit		Unit
			Min	Max	
V <sub>IO</sub>	Maximum Input Offset Voltage	V <sub>CC</sub> =5.0-30V, R <sub>S</sub> =0Ω, V <sub>O</sub> =1.4V V <sub>ICR</sub> =0V -(V <sub>CC</sub> -1.5V)* V <sub>ICR</sub> =0V -(V <sub>CC</sub> -2.0V)		7.0* 9.0	mV
I <sub>IO</sub>	Maximum Input Offset Current	V <sub>CC</sub> =5.0-30V, V <sub>O</sub> =1.4V		±50* ±150	nA
I <sub>IB</sub>	Maximum Input Bias Current	V <sub>CC</sub> =5.0-30V, V <sub>O</sub> =1.4V		-250* -500	nA
V <sub>ICR</sub>	Input Common Mode Voltage Range	V <sub>CC</sub> =30V	0 0	V <sub>CC</sub> -1.5V* V <sub>CC</sub> -2.0V	V
I <sub>CC</sub>	Maximum Power Supply Current	R <sub>L</sub> =∞, V <sub>CC</sub> =30V, V <sub>O</sub> =15V R <sub>L</sub> =∞, V <sub>CC</sub> =5V, V <sub>O</sub> =2.5V		2 1.2	mA
A <sub>VOL</sub>	Minimum Large Signal Open-Loop Voltage Gain	V <sub>CC</sub> =15V, R <sub>L</sub> =2KΩ	25* 15		V/mV
V <sub>OH</sub>	Minimum Output High-Level Voltage Swing	V <sub>CC</sub> =5V, R <sub>L</sub> =2KΩ* V <sub>CC</sub> =30V, R <sub>L</sub> =2KΩ V <sub>CC</sub> =30V, R <sub>L</sub> =10KΩ	3.3* 26 27		V
V <sub>OL</sub>	Maximum Output Low-Level Voltage Swing	V <sub>CC</sub> =5V, R <sub>L</sub> =10KΩ		20	mV
CMR	Common Mode Rejection	V <sub>CC</sub> =5-30V, R <sub>S</sub> =10KΩ	65*		dB
PSR	Power Supply Rejection	V <sub>CC</sub> =5-30V	65*		dB
I <sub>SC</sub>	Maximum Output Short Circuit to GND	V <sub>CC</sub> =5.0V, V <sub>O</sub> =0V		60*	mA
I <sub>O+</sub>	Minimum Source Output Current	V <sub>CC</sub> =15V, V <sub>ID</sub> =1.0V	20*		mA
I <sub>O-</sub>	Minimum Output Sink Current	V <sub>CC</sub> =15V, V <sub>O</sub> =15V, V <sub>ID</sub> =-1.0V V <sub>CC</sub> =15V, V <sub>O</sub> =0.2V, V <sub>ID</sub> =-1.0V	10* 12*		mA μA
V <sub>IDR</sub>	Differential Input Voltage Range	All V <sub>IN</sub> ≥GND or V-Supply (if used)		V <sub>CC</sub> *	V

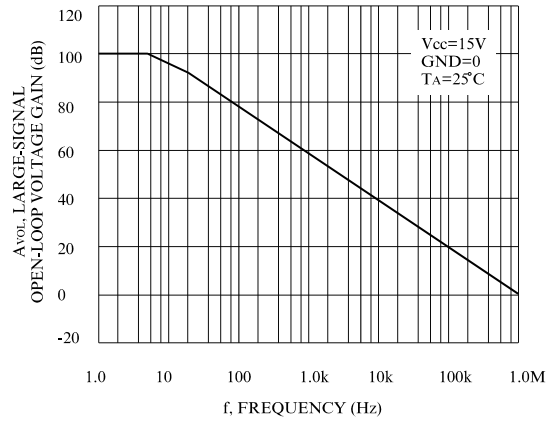
\* T<sub>A</sub>= +25°C

**NOTE:** Guaranteed Limits of DC Electrical Characteristics are given for T<sub>A</sub>=0, +70°C as the information for chips

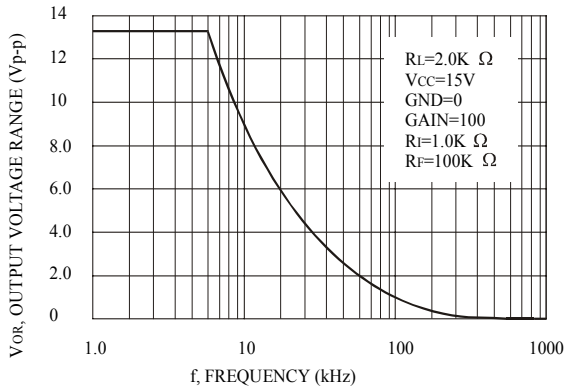
## TYPICAL PERFORMANCE CHARACTERISTICS ( $T_A = +25^\circ\text{C}$ )



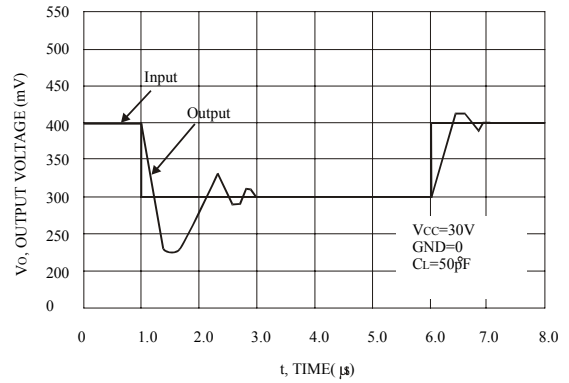
**Figure 1. Input Voltage Range**



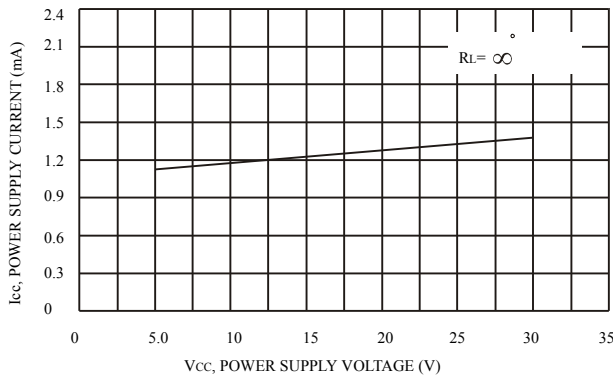
**Figure 2. Open-Loop Frequency**



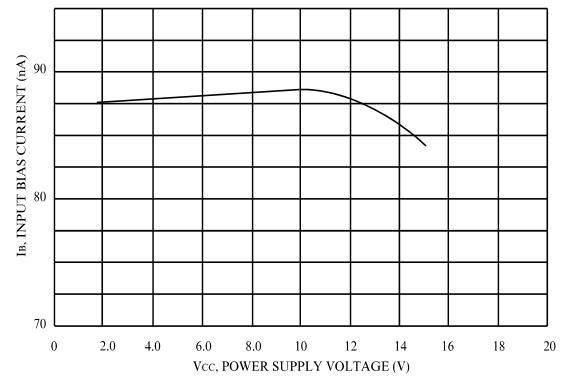
**Figure 3. Large-Signal Frequency Response**



**Figure 4. Small-Signal Voltage Follower Pulse Response (Noninverting)**



**Figure 5. Power Supply Current versus Power Supply Voltage**



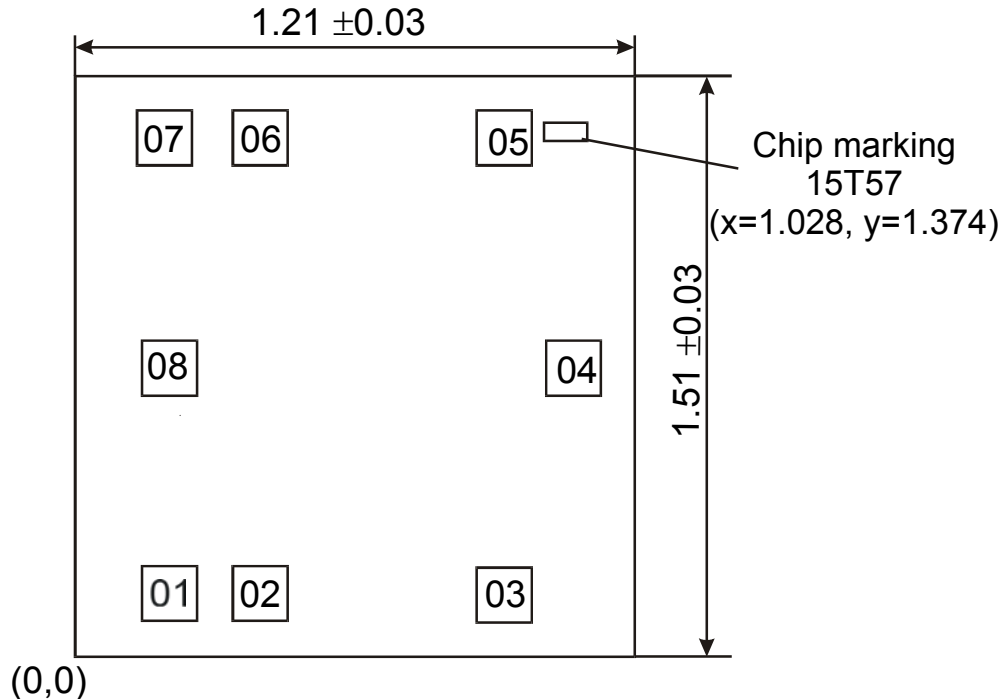
**Figure 6. Input Bias Current versus Power Supply Voltage**

## IL358N

### TYPICAL DC ELECTRICAL CHARACTERISTICS ( $T_A = +25^\circ\text{C}$ )

Symbol	Parameter	Test Conditions	Value	Unit
$\Delta V_{IO}/\Delta T$	Input Offset Voltage Drift	$R_S=0\Omega, V_{CC}=30V$	7.0*	$\mu V/^\circ\text{C}$
$\Delta I_{IO}/\Delta T$	Input Offset Current Drift	$R_S=0\Omega, V_{CC}=30V$	10*	$nA/^\circ\text{C}$
CS	Channel Separation	$f=1\text{KHz} \div 20\text{KHz}, V_{CC}=30V$	-120	dB

\*  $T_A = 0 \div +70^\circ\text{C}$



#### CHIP PAD DIAGRAM IZ358

Pad size 0.110 x 0.110 mm (Pad size is given as per passivation layer)

Thickness of chip  $0.35 \pm 0.02$  mm

#### PAD LOCATION

PAD NO	Symbol	X	Y
01	OUT1	0.087	0.085
02	IN1(-)	0.267	0.085
03	IN1(+)	0.852	0.085
04	GND	1.003	0.695
05	IN2(+)	0.852	1.305
06	IN2(-)	0.267	1.305
07	OUT2	0.087	1.305
08	$V_{CC}$	0.087	0.695